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Atomic Layer deposition for microchannel plate applications

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Brief Bio

Jeff Elam is a Senior Chemist and Group Leader at Argonne National Laboratory where he directs a program in atomic layer deposition (ALD) technology

Anil Mane is a Principal Materials Science Engineer at Argonne involved in research and development of next generation photodetectors, 2D materials, functional coatings by ALD/CVD techniques

Ashwin Jayaraman is a Postdoctoral Appointee in Argonne National Laboratory's Applied Materials Division working in Jeff Elam's group.



Microchannel Plates and Operating Principle



Readout

MCP – A continuous 2d array of 10⁴ to 10⁷ micron sized pores, which act as electron amplifiers.

Typical MCPs have a

- 1. Length over diameter (L/D) ratio of 40:1–80:1
- 2. Bias angles of 8°-20°
- 3. Pore diameters from 10 μm to 40 μm , and
- 4. Open-area ratios ranging from 60% to 83%

[1] J. L. Wiza, "Microchannel plate detectors," *Nucl. Instrum. Methods*, vol. 162, p. 587, 1979.





Microchannel Plate Photo-detector



C. Ertley et al., "Microchannel Plate Imaging Detectors for High Dynamic Range Applications," IEEE Trans. Nucl. Sci., vol. 64, no. 7, pp. 1774–1780, Jul. 2017.





Microchannel Plate Applications

- 1. Electron spectroscopy and microscopy devices,
- 2. Photomultiplier tubes (PMTs)
- 3. Medical imagers
- 4. Night vision products
- 5. Cathode ray tubes, image intensifier tubes
- 6. Time-of-flight (ToF) mass spectrometers
- 7. Photon counting, imaging microchannel plate sensors are widely used in astronomy, high energy physics and remote sensing
- 8. Sensing of photons, charged particles, and neutrons accomplished using high detection efficiency photocathodes
- 9. For space science applications, Large UV/Optical/Infrared Surveyor (LUVOIR) and the Habitable Exoplanet Imaging Mission (HABEX)



https://www.azosensors.com/equipment-details



Conventional Microchannel Plate Fabrication



[1] J. L. Wiza, "Microchannel plate detectors," Nucl. Instrum. Methods, vol. 162, p. 587, 1979



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ALD Approach for Large Area Photodetectors (LAPPD) at Argonne



- 1. Precursor introduced separately in time and space
- 2. Involves self-limiting film growth via alternate saturated surface reactions
- 3. Produces wide range of stoichiometric conformal pinhole free films
- 4. Extremely accurate thickness and composition control of mixed oxides, graded layerS
- 5. Lower deposition temperature can be used for sensitive substrates than in CVD
- 6. Low impurity level of the films enable excellent physical and chemical properties

Argonne LAPPD Approach	
≻Start w	vith porous, non-lead substrate
≻ALD (re	esistive + SEE layer) coating
≻Therm	al treatment
≻Top/B	ottom Electrode coating (NiCr)
Advan	tages
≻Indepe SEE coat	ndent control over composition of Resistive and ing
≻Low th	ermal runaway
≻Applic	able: Ceramics, SiO2, plastics, polymers MCPs
≻Low co	ost (No major issue for scale-up with ALD)
	Bare MCP ALD (R+SEE) Electrode (NiCr)

"Made in USA" capabilities Economical



Optimization of dose purge parameters and linearity in growth



Elam et al, Rev. Sci. Instrum., Vol. 73, No. 8, August 2002

Elam et al, Chem. Mater., Vol. 15, No. 4, 2003





1 um

200 nm

ALD MCP schematic and cross section showing composition



Figure 1. Schematic of basic operation of MCP.

Composed of a) resistive material, b) secondary electron emissive material and c) contact electrodes



Fabrication sequence of MCP – a) as received capillary glass array substrate, b)plan view SEM of capillary array front surface, c) Schematic cross section of fully functionalized MCP, d) Schematic cross section of individual MCP pore after ALD functionalization

A.U. Mane et.al. Physics Procedia 37 (2012) 722 – 732 - An atomic layer deposition method to fabricate economical and robust large area microchannel plates for photodetectors





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Material requirements for ALD MCP

- 1. Dry and clean porous substrates (Micro-capillary arrays)
- 2. Uniform and conformal deposition of desire materials by ALD -Stable resistive material layer (to generate electrostatic field)
- 3. Material resistivity range =1e6-1e10 Ω -cm
- 4. Stable secondary electron emission layer (signal amplification)
- 5. Stable Contact electrode (e.g NiCr, W, TiN, etc.) for electrical contact) especially by PVD electrode penetration normally a pore diameter)





ALD Chemistries for Resistive Coatings

ALD of M-Al₂O₃ Composite Films

- Combine 2 ALD processes:
 - − Oxide -- TMA/H₂O → Al₂O₃ : insulator, ρ =10¹⁶ Ωcm
 - − Metal -- MF_6/Si_2H_6 → M=W, Mo : conductor, ρ =10⁻⁴ Ωcm



- Adjust resistivity with M/(M+Al₂O₃) cycle ratio
- Deposition Temperature
- Precursors types

- 1. Mid range resistivity targeted 1e6 to 1e10 ohmcm
- 2. Thin film Material engineered by ALD
- 3. Previous Materials AlZnOx, NiAlOx, CuAlOx, TaZrOx etc
- 4. Issues: Resistivity control, Stability, Precursors nature, cost
- 5. Current method affords tunable resistance with compatible growth of mixed layers in high aspect ratio strutures



Cross section TEM image of W:Al₂O₃ composite Mane et al. – Proc SPIE 2013, Cremer et al. – Proc SPIE 2019





Resistive Materials for MCP - Properties





WAIFOC resistive material resistivity as a function of metal content

Mo:Al₂O₃ resistive material resistivity as a function of metal content

TCR values versus resistivity for M:Al2O3 tunable resistance coatings where M=Mo, W and Nb

Mane et al. – Proc SPIE 2013, Cremer et al. – Proc SPIE 2019





Alternative resistive material : ReAl₂O₃CH₃



Cross sectional Transmission Electron Microscopy image of ALD Re $Al_2O_3CH_3$ sample grown on Si(100) at 150 °C



X ray diffraction pattern of 70 nm ALD $ReAl_2O_3CH_3$ film prepared at 150 C on Si (100) as deposited (bottom) and after 400 °C anneal (top)



Resistivity as a function of metal cycles - ALD ReAl₂O₃CH₃



TCR as a function of resistivity – A comparison





Secondary electron emissive layers for MCP



Electron gain as a function of primary electron energy

Electron gain as a function of sample thickness

Electron gain as a function of surface composition

Jokela *et al*, Physics Procedia 37 (2012) 740 – 747





Cross Sectional Microstructure and roughness of ALD WAIFOC resistive layer and AI_2O_3 Secondary electron emissive layer based MCP







High Gain MCPs obtained





Phosphor image

Single MCP Image (Phosphor)

Image of 185nm UV light, **ALD MCP pair, 20µm** pores, 8° bias, 60% OAR, shows top MCP hex modulation and faint MCP hexagonal modulation from bottom MCP

Gain map



Background counts

3000 sec background, 0.0845 events/cm²/sec at 7 x 10^{6} gain, 1050v bias each MCP

High gain uniformity and low background





MCP Quantum Efficiency and gain curves





Quantum efficiency of ALD MCPs vs conventional MCPs

Gain characteristics for a 33 mm Al_2O_3 SEE ALD MCP - 20 micron pore, 60:1 L:D during burn in using 200 eV electrons



Gain characteristics for a 33 mm MgO SEE ALD MCP - 20 micron pore, 60:1 L:D during burn in using 200 eV electrons

Siegmund et al. – Performance characteristics of atomic layer functionalized microchannel plates PROC SPIE 2013





Large Area MCPs for industry



Integrated image using 185 nm illumination for a pair of 200 mm square ALD MCPs (20 µm pore, borosilicate, 60:1 L/d, 8° bias). Inter-MCP 0.7 mm gap with 200v bias.



Relative Gain

Relative

X Histogram

Y Histogram

Integrated gain map using 185 nm illumination for a pair of 200 mm square ALD MCPs (20 µm pore, borosilicate, 60:1 L/d, 8° bias). Inter-MCP 0.7 mm gap with 200v bias.

Overall gain histograms for the limage on left. Each MCP has a 1000 V bias giving an average gain of 6.5e6. Variations are modest, given the large MCP area.

Distance (pixels)

Distance (pixels)

Siegmund et al. – Performance characteristics of atomic layer functionalized microchannel plates PROC SPIE 2013



Conclusion

- 1. MCP Operating Principle and Applications Discussed
- 2. Conventional MCP drawbacks and need for ALD MCPs highlighted
- 3. ALD MCP resistive and emissive materials, properties and synthesis described
- 4. High Q.E and gain MCPs fabricated





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